



SANYO Semiconductors

DATA SHEET

N-Channel Silicon MOSFET

2SK4199LS — General-Purpose Switching Device Applications

Features

- Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- Adoption of high reliability HVP process.
- Attachment workability is good by Mica-less package.
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at $T_a=25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		650	V
Gate-to-Source Voltage	V_{GS}		± 30	V
Drain Current (DC)	I_{DC}		3	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	12	A
Allowable Power Dissipation	P_D		2.0	W
		$T_c=25^{\circ}\text{C}$ (SANYO's ideal heat dissipation condition*1)	28	W
Channel Temperature	T_{ch}		150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}		-55 to $+150$	$^{\circ}\text{C}$
Avalanche Energy (Single Pulse) *2	E_{AS}		26.4	mJ
Avalanche Current *3	I_{AV}		3	A

Note : *1 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

*2 $V_{DD}=99\text{V}$, $L=5\text{mH}$, $I_{AV}=3\text{A}$ *3 $L \leq 5\text{mH}$, single pulse

Marking : K4199

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2SK4199LS

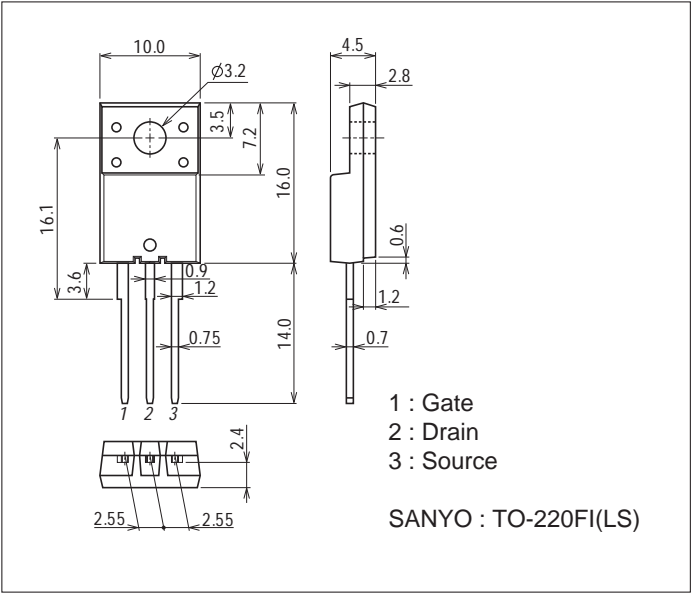
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=10mA, V_{GS}=0V$	650			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=520V, V_{GS}=0V$			100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$			± 100	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	3		5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=1.5A$	0.75	1.4		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=1.5A, V_{GS}=10V$		3.0	3.9	Ω
Input Capacitance	C_{iss}	$V_{DS}=30V, f=1MHz$		260		pF
Output Capacitance	C_{oss}	$V_{DS}=30V, f=1MHz$		47		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=30V, f=1MHz$		9.3		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		12		ns
Rise Time	t_r	See specified Test Circuit.		19		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		28		ns
Fall Time	t_f	See specified Test Circuit.		13		ns
Total Gate Charge	Q_g	$V_{DS}=200V, V_{GS}=10V, I_D=3A$		10.3		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=200V, V_{GS}=10V, I_D=3A$		2.4		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=200V, V_{GS}=10V, I_D=3A$		5.7		nC
Diode Forward Voltage	V_{SD}	$I_S=3A, V_{GS}=0V$		0.9	1.2	V

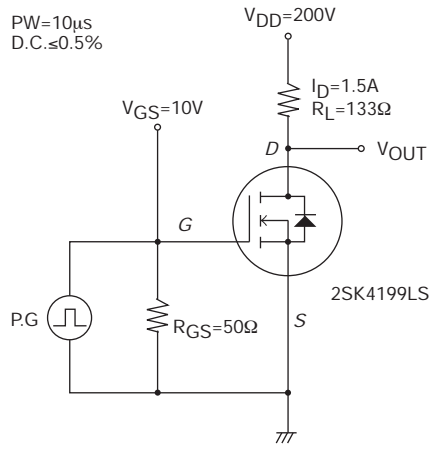
Package Dimensions

unit : mm (typ)

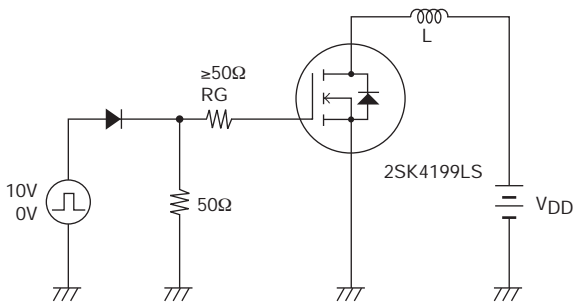
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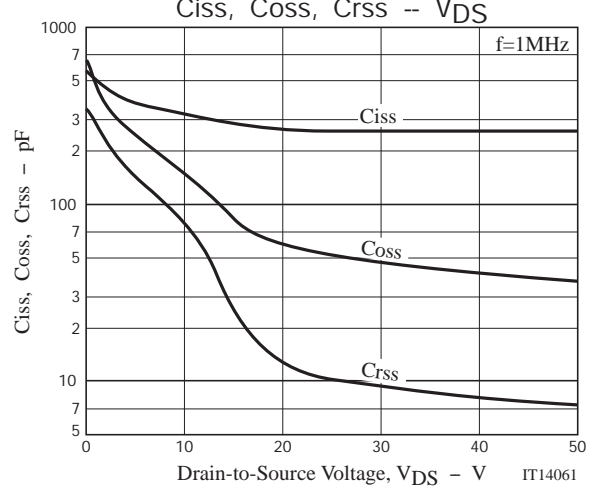
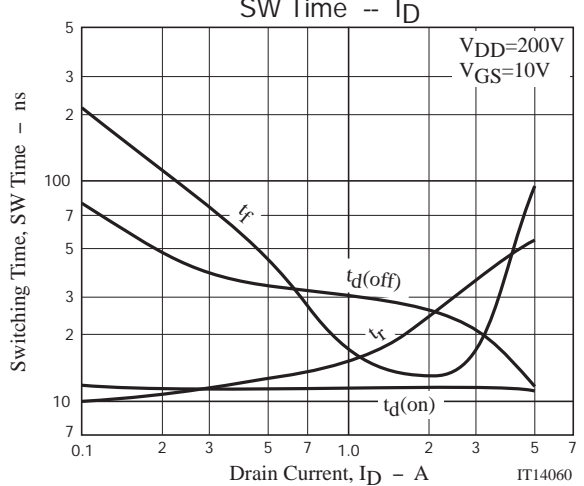
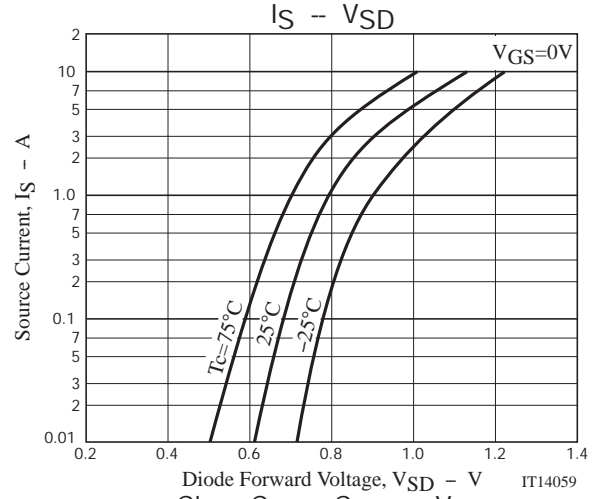
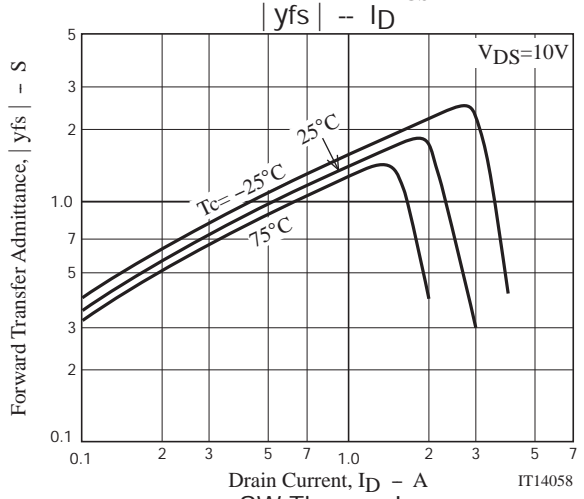
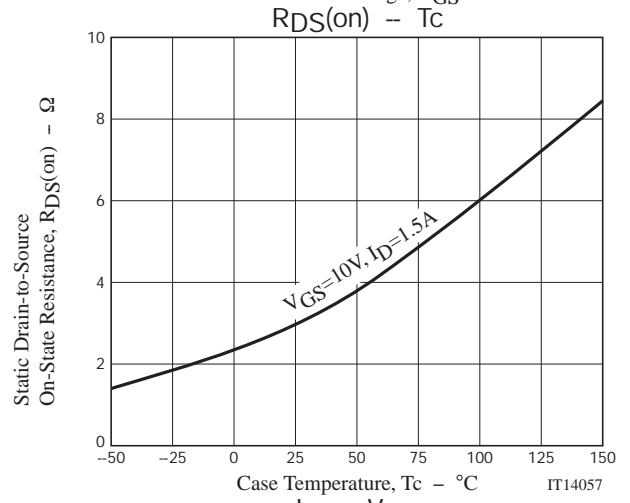
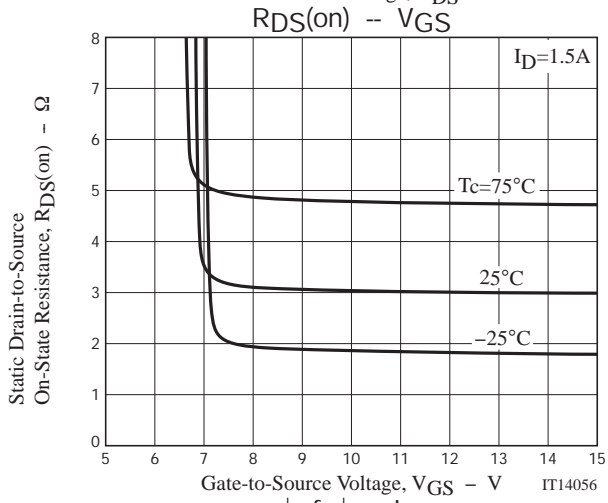
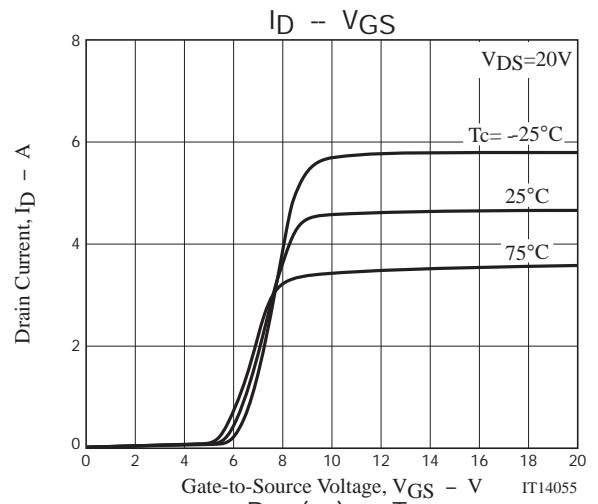
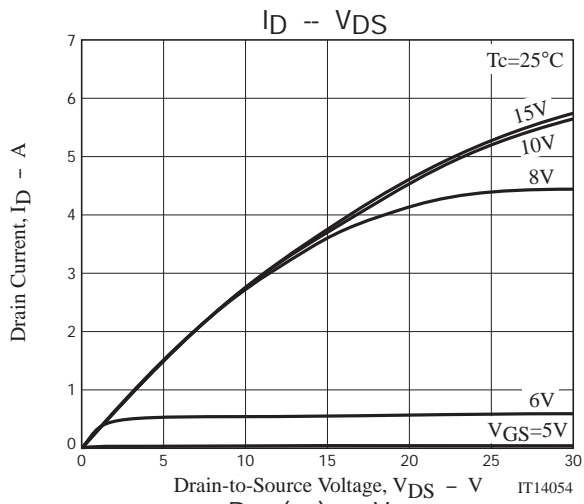


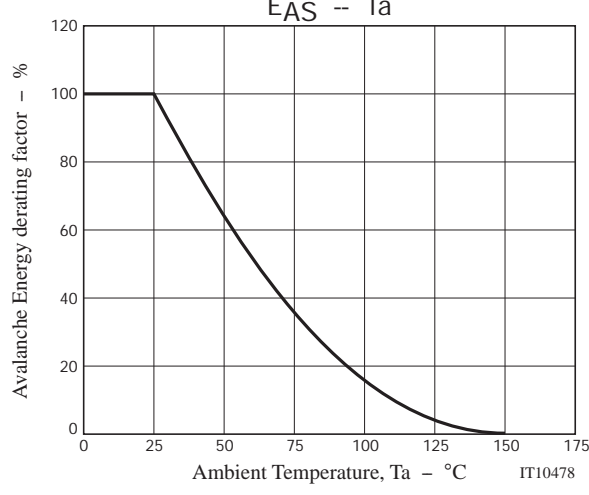
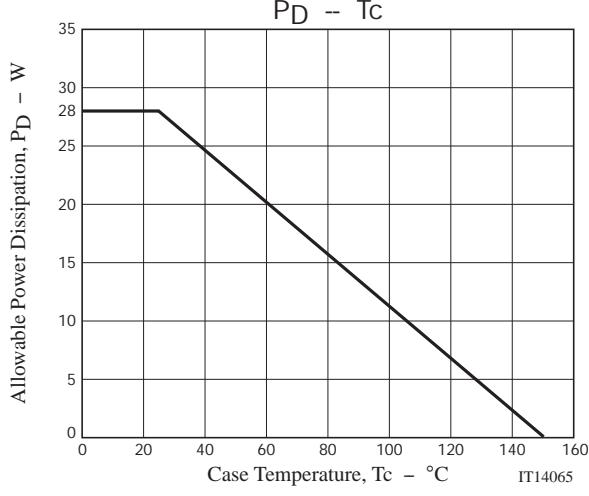
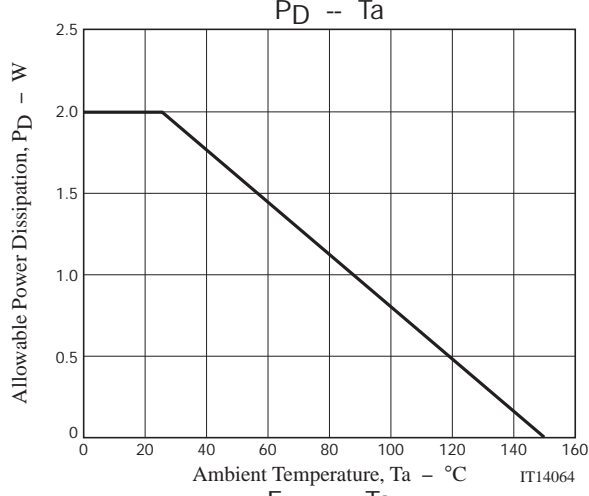
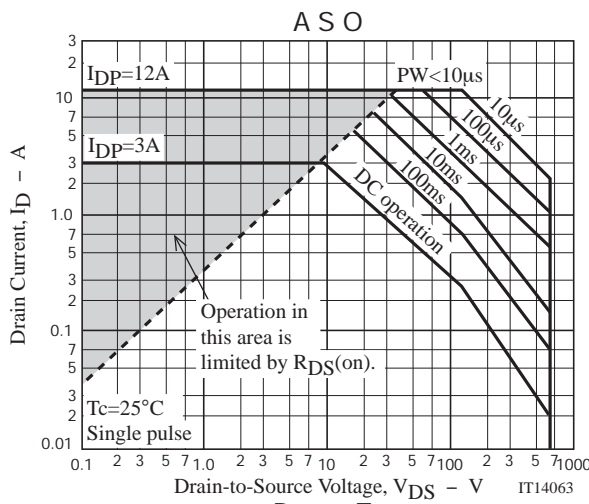
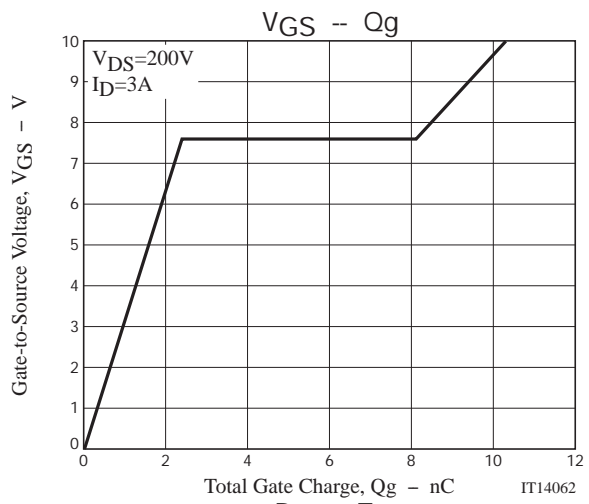
Switching Time Test Circuit



Avalanche Resistance Test Circuit







Note on usage : Since the 2SK4199LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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